

REMARKS

Claims 1, 44-48, and 55-84 are pending, of which claims 1 and 44-48 are independent. Claims 44 and 61-66 are amended in response to objections thereto, and Applicant requests that the objections to these claims be withdrawn accordingly. Claims 49-54 are cancelled. FIG. 5 has been amended as shown in the attached Replacement and Annotated Sheets, and as discussed in more detail, below. No new matter has been added.

Claims 49-54 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite. Applicant respectfully submits that this rejection is obviated by the cancellation of claims 49-54, and requests that the rejection be withdrawn.

Claims 1, 44-48, and 55-84 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. Also, FIG. 5, as added in Applicant's response of November 3, 2003, has not been approved. Specifically, the Office Action takes the position in paragraph 2 that the previously-presented "FIG. 5 sets forth new matter because the specification as originally filed did not disclose a bottom-gate TFT." Further, the Office Action takes the position in paragraph 3 that FIG. 5 fails to "show every feature of the invention specified in the claims," including the insulating surface.

In response to (a) the rejection under 35 U.S.C. 112, first paragraph, (b) the related ruling of new matter having been presented in FIG. 5, and (c) the required drawing correction(s), Applicant respectfully submits (without agreeing that previously-presented FIG. 5 constituted or included new matter) newly-presented FIG. 5 (as shown in the attached Replacement Sheet). Further, Applicant respectfully submits that newly-presented FIG. 5 does not constitute or include new matter, and that newly-presented FIG. 5 addresses the objections to the drawings, as described above.

Support for newly-presented FIG. 5, and for pending claims 1, 44-48, and 55-84 may be found, for example, page 14, lines 1-4 of Applicant's specification, which states that "one significant advantage of the present invention lies in (its) capability of readily forming or fabricating intended field-effect transistors with functions similar to those of the LDD structure." Further, the specification discloses at page 14, lines 8-11, "... while a top-gate type thin film

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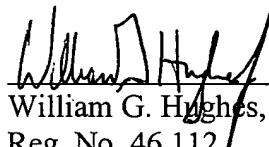
transistor has been disclosed in the preferred embodiment, the present invention can be applied to a bottom gate type transistor in which a gate electrode is located below the channel forming region.” Accordingly, Applicant respectfully submits that the techniques, reasoning, and disclosure supplied throughout Applicant’s specification in the context of the example of a top gate transistor may be applied to the example of the bottom gate type transistor, so that claims 1, 44-48, and 55-84 are supported and described within Applicant’s specification in accordance with 35 U.S.C. 112, first paragraph, and so that newly-presented FIG. 5 does not constitute new matter, but rather merely illustrates features of the invention specified in the claims and described in the specification.

Accordingly, Applicant respectfully submits that claims 1, 44-48, and 55-84 are in condition for allowance, and requests such action in the Examiner’s next official communication.

Please apply any necessary charges or credits to deposit account 06-1050.

Respectfully submitted,

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